

WHAT IS CLAIMED IS:

1. An electret comprising:
a charged silicon oxide film; and
an insulating film formed to cover the silicon oxide film.
- 5 2. The electret of claim 1, wherein the insulating film has a higher moisture resistance than the silicon oxide film.
3. The electret of claim 1, wherein the insulating film is a silicon nitride film.
4. The electret of claim 1, wherein the silicon oxide film has been charged by a plasma discharge or a corona discharge.
- 10 5. An electret condenser comprising:
a first electrode formed with through holes;
a second electrode disposed with an air gap interposed between itself and the first electrode; and
an electret composed of a charged silicon oxide film formed on a surface of the
15 second electrode which is opposing the first electrode, wherein
an insulating film is formed to cover the silicon oxide film.
6. The electret condenser of claim 5, wherein the insulating film has a higher moisture resistance than the silicon oxide film.
7. The electret condenser of claim 5, wherein the insulating film is a silicon nitride
20 film.
8. The electret condenser of claim 5, wherein the first electrode is made of silicon, polysilicon, aluminum, or an aluminum alloy.
9. The electret condenser of claim 5, wherein the second electrode is made of gold or a refractory metal.
- 25 10. The electret condenser of claim 5, wherein the silicon oxide film has been

charged by a plasma discharge or a corona discharge.

11. An electret condenser comprising:

a fixed film having a first electrode and formed with first through holes;

a second electrode disposed with an air gap interposed between itself and the

5 fixed film; and

an electret composed of a charged silicon oxide film formed on a surface of the second electrode which is opposing the fixed film, wherein

an insulating film is formed to cover the silicon oxide film.

12. The electret condenser of claim 11, wherein

10 second through holes reaching the air gap is formed in a multilayer structure composed of the second electrode and the silicon oxide film and

a silicon nitride film is formed on a surface of the silicon oxide film which forms an inner wall surface of the second through holes.

13. The electret condenser of claim 11, wherein the insulating film has a higher
15 moisture resistance than the silicon oxide film.

14. The electret condenser of claim 11, wherein the insulating film is a silicon nitride film.

15. The electret condenser of claim 11, wherein each of the first electrode and the second electrode is made of aluminum, an aluminum alloy, silicon, polysilicon, gold, or a
20 refractory metal.

16. An electric condenser comprising:

a semiconductor substrate having a region removed to leave a peripheral portion thereof; and

a vibrating film formed on the semiconductor substrate to cover the region,
25 wherein

the vibrating film has a multilayer structure composed of an electret, an electrode film, a first insulating film, and a second insulating film and

said electret is covered with each of the first insulating film and the second insulating film.

- 5 17. The electret condenser of claim 16, wherein the electrode film is formed inside the region in non-overlapping relation with the semiconductor substrate.